
2SC4260

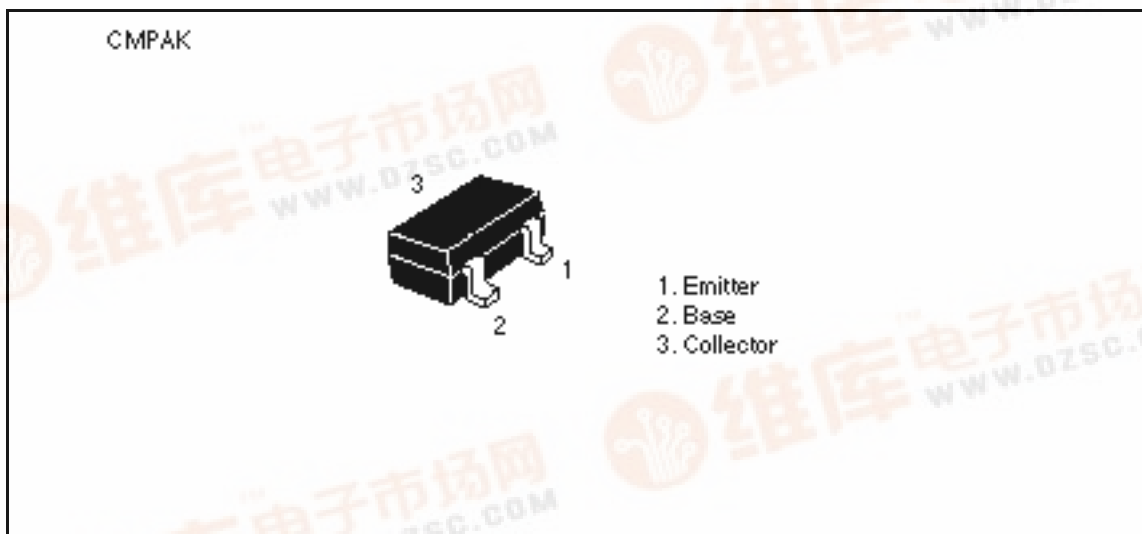
Silicon NPN Epitaxial

HITACHI

Application

UHF frequency converter, Wide band amplifier

Outline



2SC4260

Absolute Maximum Ratings (Ta = 25°C)

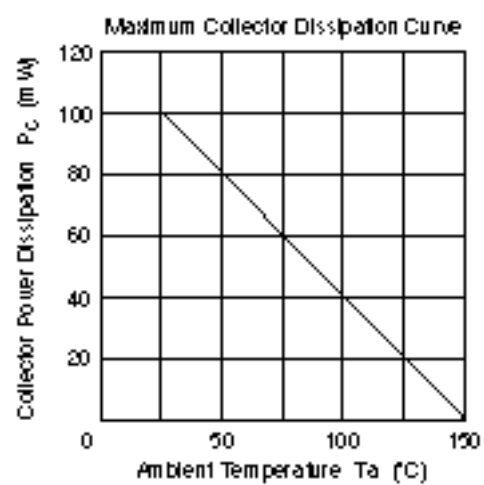
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	25	V
Collector to emitter voltage	V_{CEO}	13	V
Emitter to base voltage	V_{EBO}	3	V
Collector current	I_C	50	mA
Collector power dissipation	P_C	100	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	–55 to +150	°C

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	25	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector cutoff current	I_{CBO}	—	—	0.1	μA	$V_{CB} = 15 V, I_E = 0$
	I_{CEO}	—	—	10	μA	$V_{CE} = 13 V, R_{BE} = \bullet$
Emitter cutoff current	I_{EBO}	—	—	0.3	μA	$V_{EB} = 3 V, I_C = 0$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	0.3	V	$I_C = 20 mA, I_B = 4 mA$
DC current transfer ratio	h_{FE}	50	—	180		$V_{CE} = 5 V, I_C = 5 mA$
Collector output capacitance	C_{ob}	—	0.85	1.3	pF	$V_{CB} = 10 V, I_E = 0, f = 1 MHz$
Gain bandwidth product	f_T	3.0	3.8	—	GHz	$V_{CE} = 5 V, I_C = 5 mA$
Conversion gain	CG	—	19	—	dB	$V_{CC} = 5 V, I_C = 0.8 mA, f = 900 MHz$
Noise figure	NF	—	8	—	dB	$f_{OSC} = 930 MHz (-5dBm), f_{out} = 30 MHz$

Note: Marking is "TI—".

See characteristic curves of 2SC4197.



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HITACHI

Hitachi, Ltd.

Semiconductor & IC Div.

Nippon Bldg., 2-6-2, Ohite-machi, Chiyoda-ku, Tokyo 100, Japan

Tel: Tokyo (03) 3270-2111

Fax: (03) 3270-5109

For further information write to:

Hitachi America, Ltd.

Semiconductor & IC Div.

2000 Sierra Point Parkway

Berkeley, CA 94705-4835

U.S.A.

Tel: 415-589-8300

Fax: 415-589-4207

Hitachi Europe GmbH

Electronic Components Group

Continental Europe

Danrecher Straße 3

D-85622 Feldkirchen

München

Tel: 089-9 91 80-0

Fax: 089-9 29 30 00

Hitachi Europe Ltd.

Electronic Components Div.

Northern Europe Headquarters

Whitbrook Park

Lower Cookham Road

M Maidenhead

Berkshire SL6 6YU

United Kingdom

Tel: 0628-585000

Fax: 0628-778322

Hitachi Asia Pte. Ltd.

45 Collyer Quay #20-00

Hitachi Tower

Singapore 0104

Tel: 535-2100

Fax: 535-1533

Hitachi Asia (Hong Kong) Ltd.

Unit 705, North Tower,

World Finance Centre

Harbour City, Canton Road

Tsim Sha Tsui, Kowloon

Hong Kong

Tel: 27359218

Fax: 27308074